

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	27	("20020063292" "20030032261" "20030040158" "20040238914" "20040262784" "20050040460" "20050082634" "20050093030" "20050098829" "20050106799" "20050145954" "20050148146" "20050194699" "20050236668" "20050245017" "20050280051" "20050282325" "20060027868" "20060057787" "20060060925" "6483171" "6717216" "6825529" "6831292" "6974981" "6977194" "7015082"). PN.	US-PGPUB; USPAT	OR	OFF	2006/08/01 09:58
L2	2	jp-01076755-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/08/01 09:15
L6	207	438/218.ccls.	US-PGPUB; USPAT	OR	OFF	2006/08/01 11:05
L7	2665	438/199.ccls. 438/218.ccls. 438/221.ccls. 438/514.ccls. 438/739.ccls. 438/766.ccls.	US-PGPUB; USPAT	OR	OFF	2006/08/01 11:13
L8	13302	((silicon adj (germanium oxide dioxide nitride oxynitride)) sige gesi "sio.sub.2" sin sion "si.sub.3 n.sub.4" sio "si.sub.3n.sub.4" "sio.sub.x n.sub.y" "sio.sub.xn.sub.y") with (strain stress tens\$6 compress\$6)	US-PGPUB; USPAT	OR	ON	2006/08/01 11:13
L9	246	L7 and L8	US-PGPUB; USPAT	OR	ON	2006/08/01 11:13
L10	2804	((silicon adj (germanium oxide dioxide nitride oxynitride)) sige gesi "sio.sub.2" sin sion "si.sub.3 n.sub.4" sio "si.sub.3n.sub.4" "sio.sub.x n.sub.y" "sio.sub.xn.sub.y") with (strain stress tens\$6 compress\$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 12:01
L11	925	L10 and (etch\$6 gap groove trench slot hole opening dop\$6 implant\$8)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 12:01
L12	104	L11 and (cmos nmos pmos nfet pfet "n-type" "p-type") and (semiconductor substrate wafer silicon)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 12:01

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L13	1578	((silicon adj (germanium oxide dioxide nitride oxynitride)) sige gesi "sio.sub.2" sin sion "si.sub.3 n.sub.4" sio "si.sub.3n.sub.4" "sio.sub.x n.sub.y" "sio.sub.xn.sub.y") with ((strain stress tens\$6 compress\$6) near (layer film))	US-PGPUB; USPAT	OR	ON	2006/08/01 12:06
L14	126	L13 same (cmos nmos pmos nfet pfet "n-type" "p-type") same (semiconductor substrate wafer silicon)	US-PGPUB; USPAT	OR	ON	2006/08/01 12:28
L15	119	L13 same (etch\$6 remov\$6) same (gap groove trench slot hole opening dop\$6 implant\$6)	US-PGPUB; USPAT	OR	ON	2006/08/01 12:20
L16	59	((((strain stress tens\$6 compress\$6) near2 (layer film)) and (cmos nmos pmos nfet pfet "n-type" "p-type" complementary) and (semiconductor substrate wafer silicon) and ((etch\$6 remov\$6 form\$6) with (gap groov\$6 trench slot hole open\$6 aperture))))).clm.	US-PGPUB	OR	ON	2006/08/01 12:32